

PNP HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/ 379

Devices

2N3791

2N3792

Qualified Level

JAN
JANTX
JANTXV

MAXIMUM RATINGS

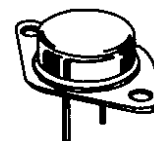
Ratings	Symbol	2N3791	2N3792	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Base Current	I_B	4.0		Adc
Collector Current	I_C	10		Adc
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$ ⁽¹⁾ @ $T_C = +100^{\circ}\text{C}$ ⁽²⁾	P_T	5.0		W
		85.7		W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.17	$^{\circ}\text{C/W}$

1) Derate linearly @ 28.57 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly @ 0.857 mW/ $^{\circ}\text{C}$ for $T_C > +100^{\circ}\text{C}$



TO-3*
(TO-204AA)

*See Appendix A for
Package Outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
-----------------	--------	------	------	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	2N3791	$V_{(BR)CEO}$	60	Vdc
	2N3792		80	
Collector-Emitter Cutoff Current $V_{CE} = 50 \text{ Vdc}$ $V_{CE} = 70 \text{ Vdc}$	2N3791	I_{CES}	5.0	mAdc
	2N3792		5.0	
Collector-Emitter Cutoff Current $V_{CE} = 60 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$ $V_{CE} = 80 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$	2N3791	I_{CEX}	5.0	mAdc
	2N3792		5.0	

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
Collector-Base Cutoff Current V _{CB} = 60 Vdc V _{CB} = 80 Vdc	I _{CBO}		5.0 5.0	mAdc
Emitter-Base Cutoff Current V _{EB} = 7.0 Vdc	I _{EBO}		5.0	mAdc

ON CHARACTERISTICS ⁽³⁾

Forward-Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 2.0 Vdc I _C = 3.0 Adc, V _{CE} = 2.0 Vdc I _C = 5.0 Adc, V _{CE} = 2.0 Vdc I _C = 10 Adc, V _{CE} = 4.0 Vdc	h _{FE}	50 30 10 5.0	150 120	
Collector-Emitter Saturation Voltage I _C = 5.0 Adc, I _B = 0.5 Adc I _C = 10 Adc, I _B = 2.0 Adc	V _{CE(sat)}		1.0 2.5	Vdc
Base-Emitter Saturation Voltage I _C = 5.0 Adc, I _B = 0.5 Adc I _C = 10 Adc, I _B = 2.0 Adc	V _{BE(sat)}		1.5 3.0	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz	h _{fe}	4.0	20	
Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz	h _{fe}	30	300	
Output Capacitance V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz	C _{obo}		500	pF

SAFE OPERATING AREA**DC Tests**T_C = +25°C, 1 Cycle, t ≥ 1.0 s**Test 1**V_{CE} = 15 Vdc, I_C = 10 Adc**Test 2**V_{CE} = 40 Vdc, I_C = 3.75 Adc**Test 3**V_{CE} = 55 Vdc, I_C = 0.9 Adc 2N3791V_{CE} = 65 Vdc, I_C = 0.9 Adc 2N3792

(3) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.